

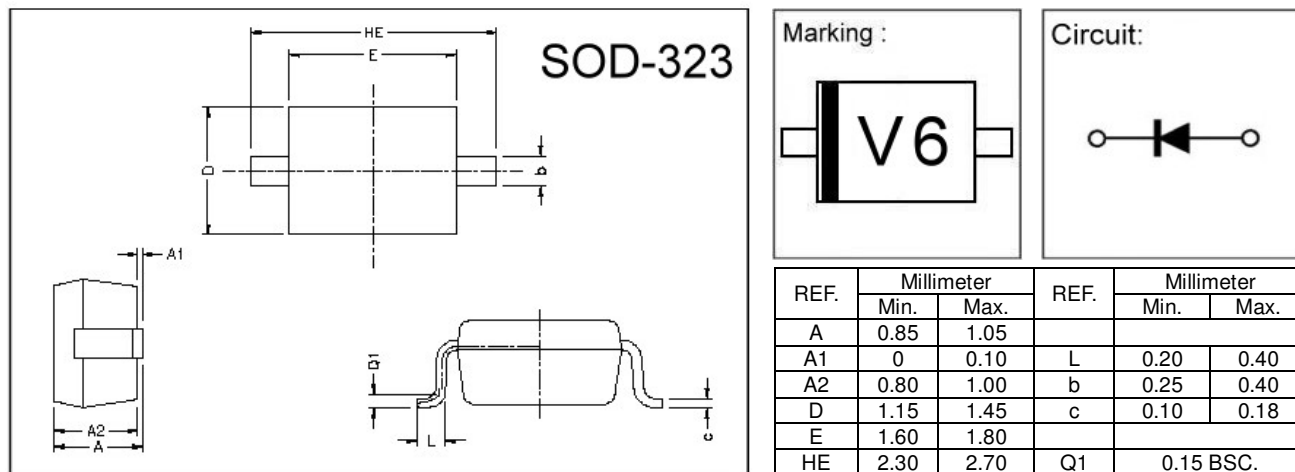
GD421SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.1A

Description

The GD421SD is designed for low power rectification.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40	V
Maximum RMS Voltage	V _{RPS}	28	V
Maximum DC Blocking Voltage	V _{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	1.0	A
Typical Junction Capacitance between Terminal	C _J	6.0	pF
Maximum Average Forward Rectified Current	I _o	0.1	A
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _{(BR)R}	40	-	-	V	I _R =50μA
Forward Voltage	V _{F(1)}	-	-	340	mV	I _F =10mA
	V _{F(2)}	-	-	550	mV	I _F =100mA
Reverse Leakage Current	I _R	-	-	30	μA	V _R =10V

Characteristics Curve

FIG. 1 - FORWARD CHARACTERISTICS

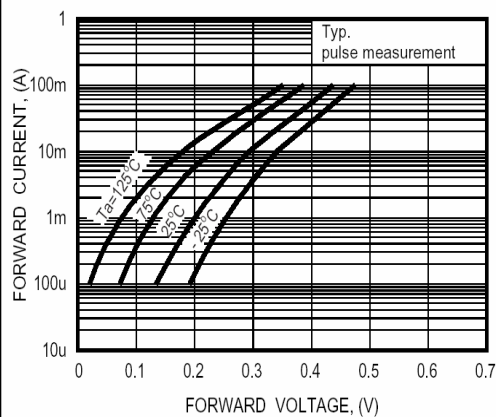


FIG. 2 - REVERSE CHARACTERISTICS

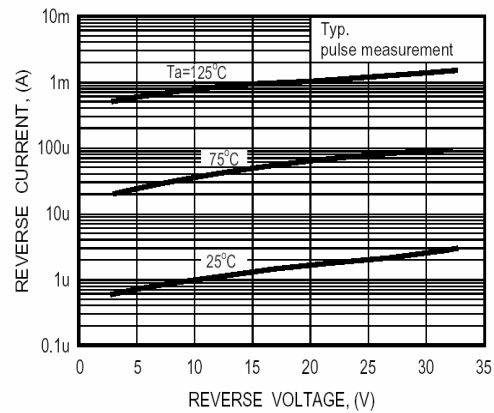


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

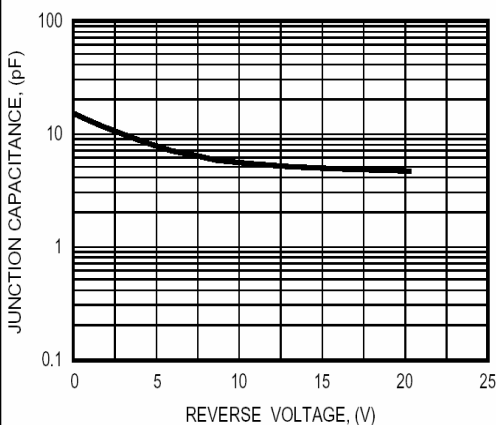
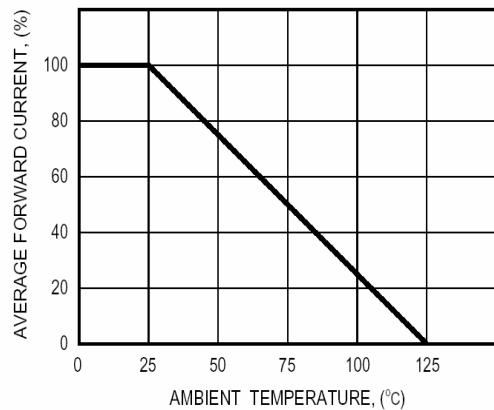


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

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